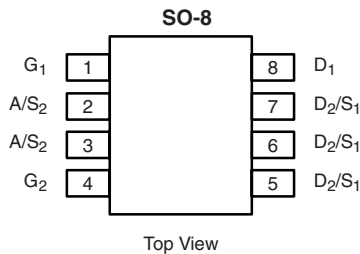


Dual N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY			
	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
Channel-1	30	0.022 at V _{GS} = 10 V	6.3
		0.030 at V _{GS} = 4.5 V	5.4
Channel-2		0.013 at V _{GS} = 10 V	10
		0.0185 at V _{GS} = 4.5 V	8.6

SCHOTTKY PRODUCT SUMMARY		
V _{DS} (V)	V _{SD} (V) Diode Forward Voltage	I _F (A)
30	0.50 V at 1.0 A	2.0

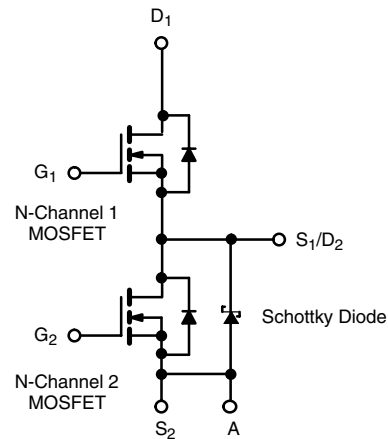


FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- LITTLE FOOT® Plus Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available



Ordering Information: Si4816DY-T1-E3 (Lead (Pb)-free)
Si4816DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted							
Parameter	Symbol	Channel-1		Channel-2		Unit	
		10 s	Steady State	10 s	Steady State		
Drain-Source Voltage	V _{DS}	30				V	
Gate-Source Voltage	V _{GS}	20					
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	6.3	5.3	10	7.7	A
		T _A = 70 °C	5.4	4.2	8.2	6.2	
Pulsed Drain Current	I _{DM}	30		40			
Continuous Source Current (Diode Conduction) ^a	I _S	1.3	0.9	2.2	1.15		
Avalanche Current ^b	L = 0.1 mH	I _{AS}	12		25		
Single Pulse Avalanche Energy ^b		E _{AS}	7.2		31.25		mJ
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	1.4	1.0	2.4	1.25	W
			T _A = 70 °C	0.9	0.64	1.5	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150				°C	

THERMAL RESISTANCE RATINGS									
Parameter	Symbol	Channel-1		Channel-2		Schottky		Unit	
		Typ.	Max.	Typ.	Max.	Typ.	Max.		
Maximum Junction-to-Ambient ^a	R _{thJA}	t ≤ 10 s	72	90	43	53	48	60	°C/W
		Steady State	100	125	82	100	80	100	
Maximum Junction-to-Foot (Drain)	R _{thJC}	51	63	25	30	28	35		

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
b. Starting date code W46BAA.

MOSFET SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted								
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit		
Static								
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	Ch-1	0.8		2	V	
			Ch-2	1.0		3		
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$	Ch-1			100	nA	
			Ch-2			100		
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	Ch-1			1	μA	
			Ch-2			100		
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$	Ch-1			15		
			Ch-2			2000		
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	Ch-1	20			A	
			Ch-2	30				
Drain-Source On-State Resistance ^b	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 6.3\text{ A}$	Ch-1		0.018	0.022	Ω	
			Ch-2	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$		0.0105		0.013
				$V_{GS} = 4.5\text{ V}, I_D = 5.4\text{ A}$	Ch-1			0.024
			Ch-2	$V_{GS} = 4.5\text{ V}, I_D = 8.6\text{ A}$		0.015		0.0185
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 6.3\text{ A}$	Ch-1		17		S	
			Ch-2		28			
Diode Forward Voltage ^b	V_{SD}	$I_S = 1.3\text{ A}, V_{GS} = 0\text{ V}$	Ch-1		0.7	1.1	V	
			Ch-2		0.47	0.5		
Dynamic^a								
Total Gate Charge	Q_g	Channel-1 $V_{DS} = 15\text{ V}, V_{GS} = 5\text{ V}, I_D = 6.3\text{ A}$	Ch-1		8.0	12	nC	
			Ch-2		15	23		
Gate-Source Charge	Q_{gs}	Channel-2 $V_{DS} = 15\text{ V}, V_{GS} = 5\text{ V}, I_D = -10\text{ A}$	Ch-1		1.75			
			Ch-2		5.3			
Gate-Drain Charge	Q_{gd}	Channel-2 $V_{DS} = 15\text{ V}, V_{GS} = 5\text{ V}, I_D = -10\text{ A}$	Ch-1		3.2			
			Ch-2		4.6			
Gate Resistance	R_g		Ch-1	1.5		6.1	Ω	
			Ch-2	0.5		2.6		
Turn-On Delay Time	$t_{d(on)}$	Channel-1 $V_{DD} = 15\text{ V}, R_L = 15\text{ }\Omega$	Ch-1		10	20	ns	
Rise Time	t_r	$I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$	Ch-2		15	30		
			Ch-1		5	10		
Turn-Off Delay Time	$t_{d(off)}$	Channel-2 $V_{DD} = 15\text{ V}, R_L = 15\text{ }\Omega$	Ch-1		26	50		
			Ch-2		44	80		
Fall Time	t_f	$I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$	Ch-1		8	16		
			Ch-2		12	24		
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 1.3\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	Ch-1		30	60		
		$I_F = 2.2\text{ A}, di/dt = 100\text{ }\mu\text{A}/\mu\text{s}$	Ch-2		32	70		

Notes:

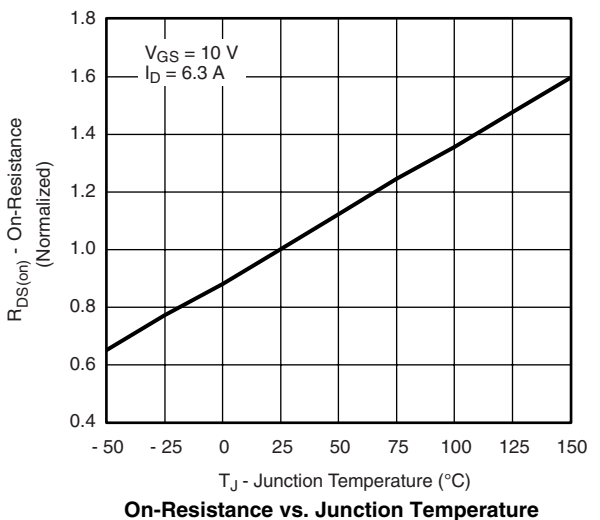
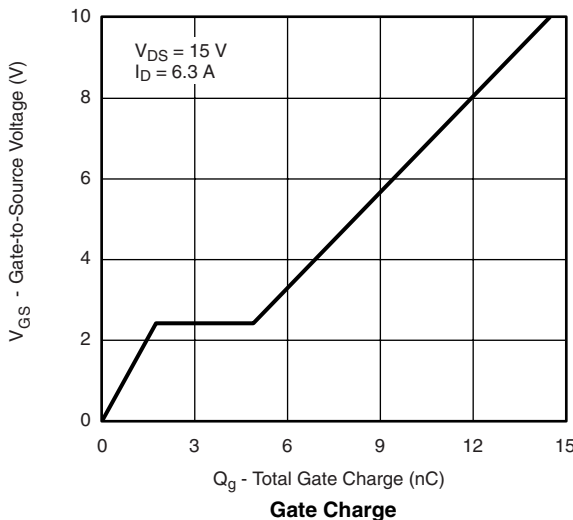
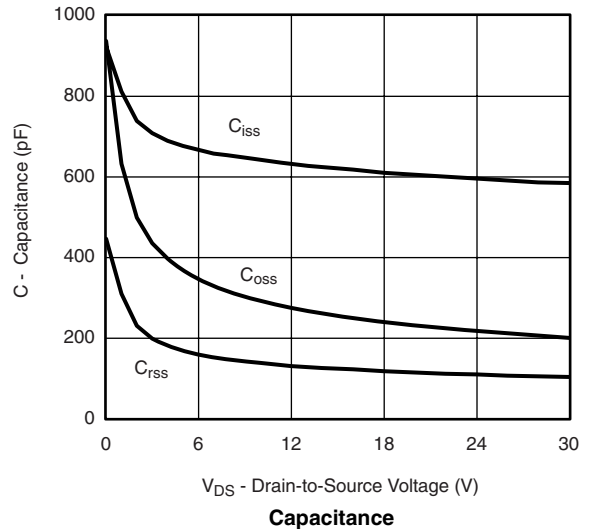
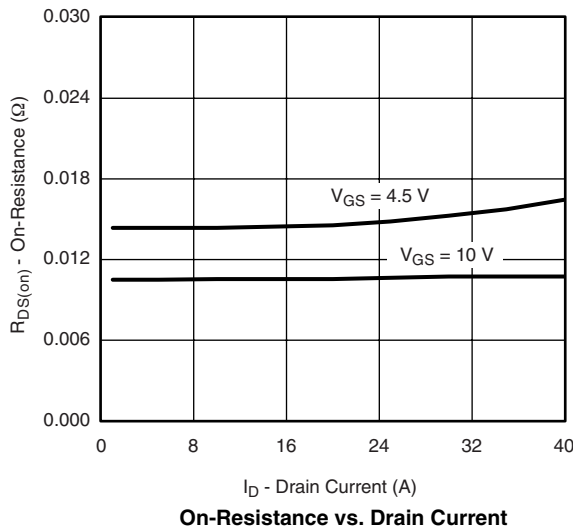
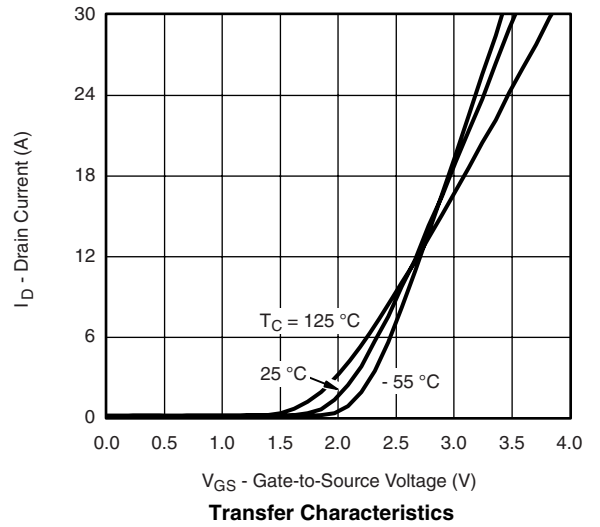
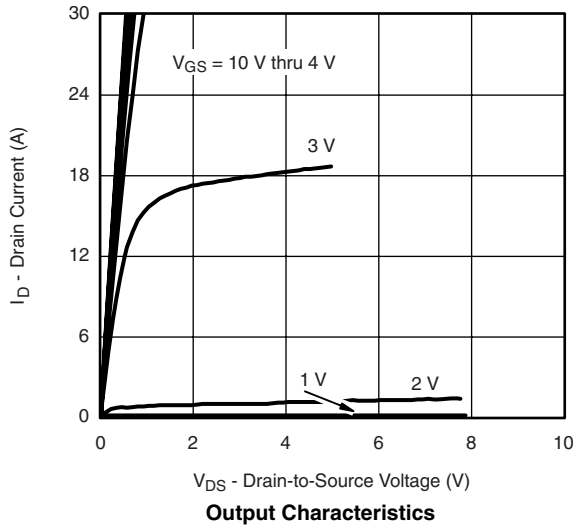
a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

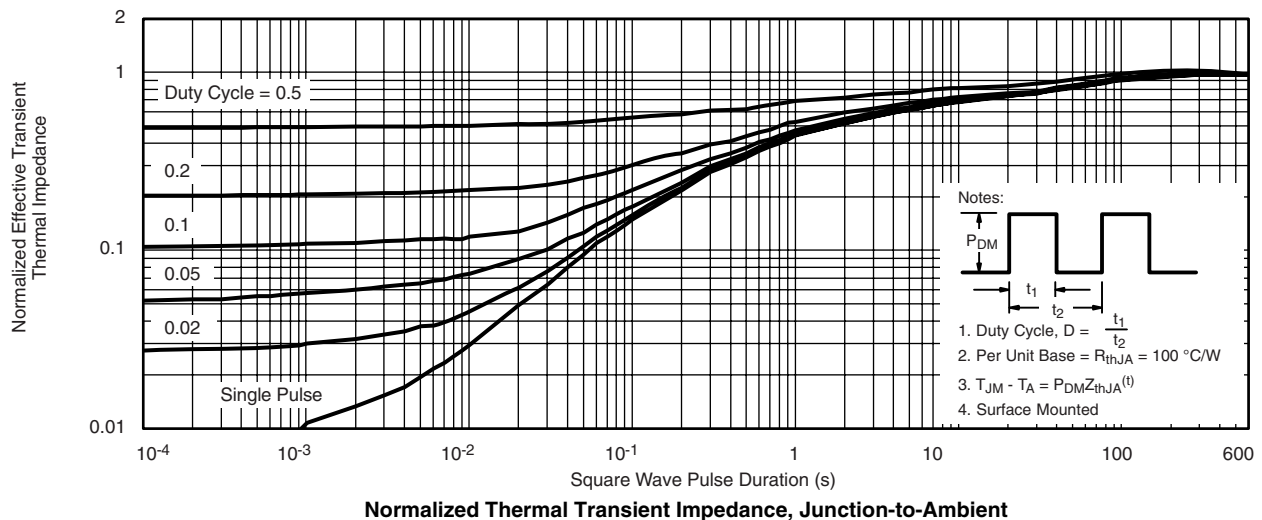
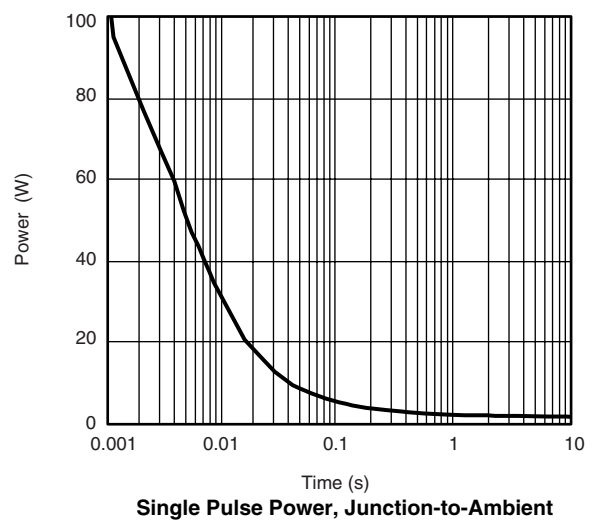
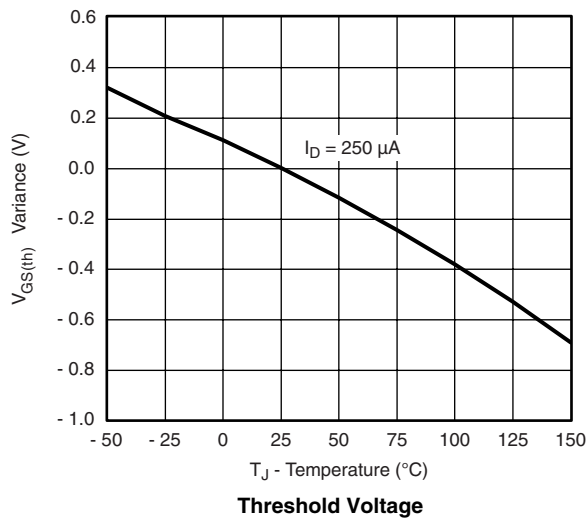
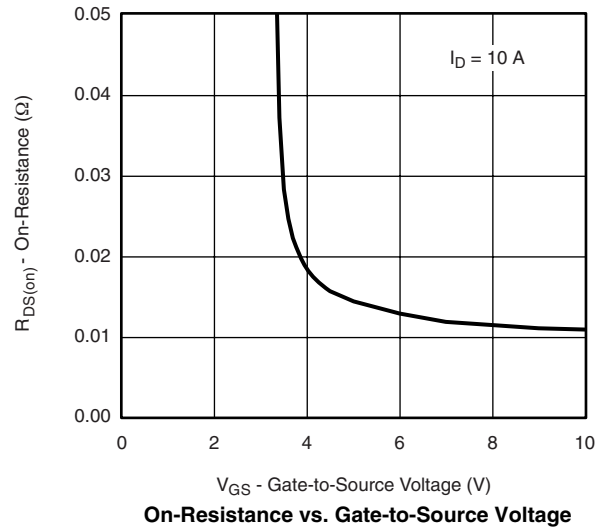
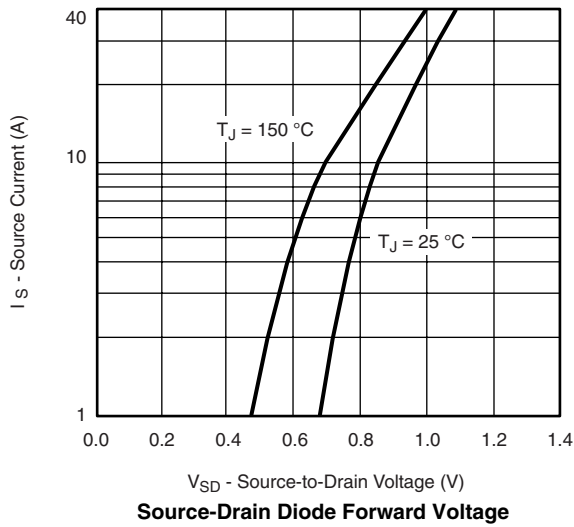
SCHOTTKY SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Forward Voltage Drop	V_F	$I_F = 1.0\text{ A}$		0.47	0.50	V
		$I_F = 1.0\text{ A}, T_J = 125\text{ }^\circ\text{C}$		0.36	0.42	
Maximum Reverse Leakage Current	I_{rm}	$V_R = 30\text{ V}$		0.004	0.100	mA
		$V_R = 30\text{ V}, T_J = 100\text{ }^\circ\text{C}$		0.7	10	
		$V_R = -30\text{ V}, T_J = 125\text{ }^\circ\text{C}$		3.0	20	
Junction Capacitance	C_T	$V_R = 10\text{ V}$		50		pF

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

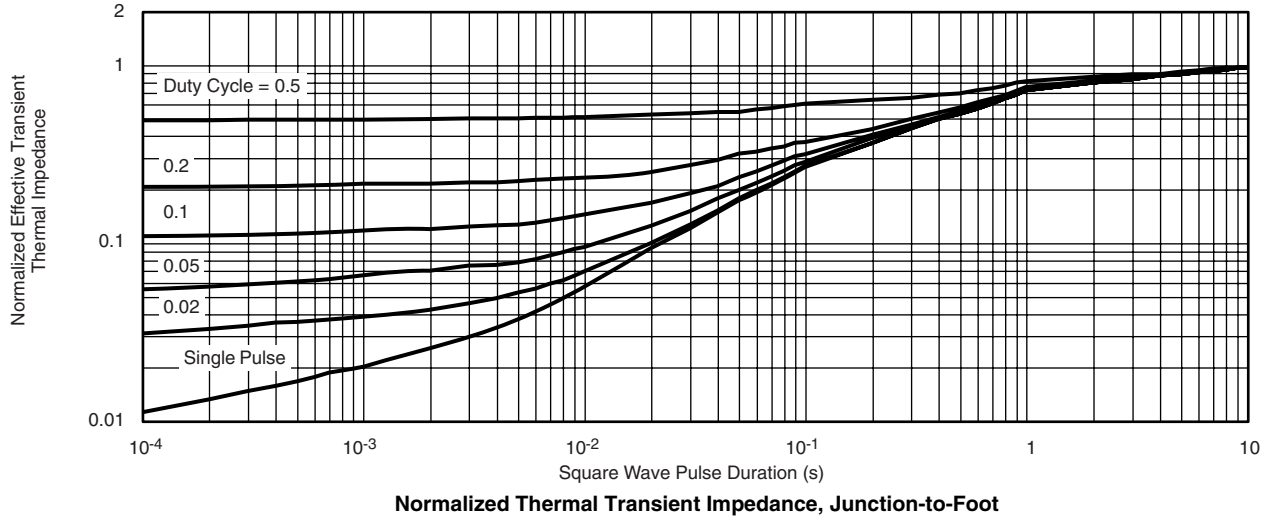
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



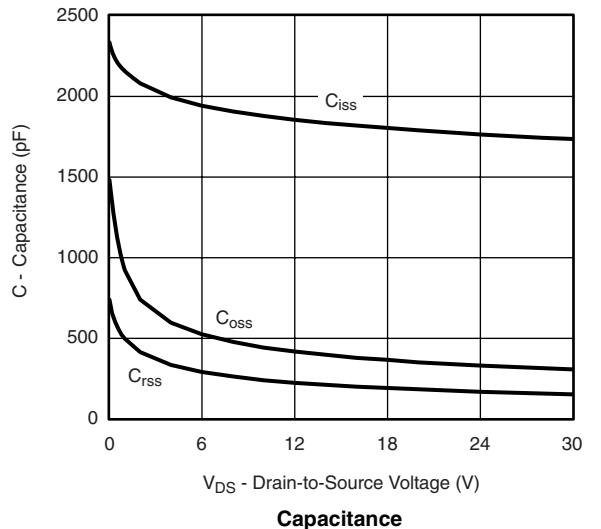
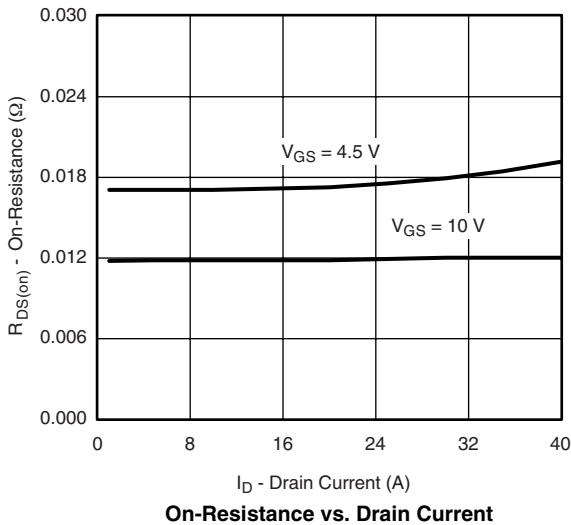
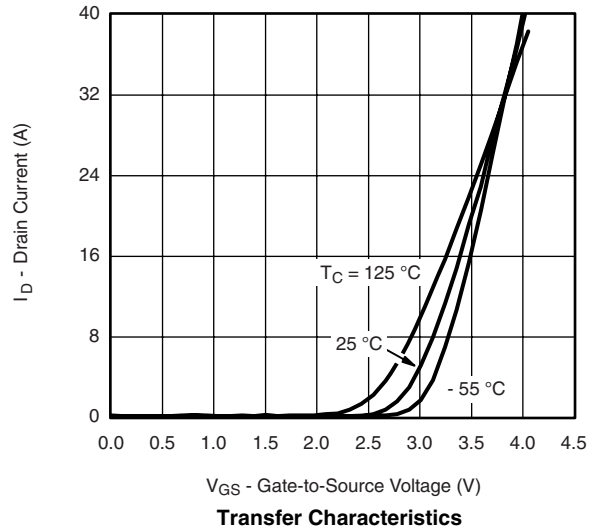
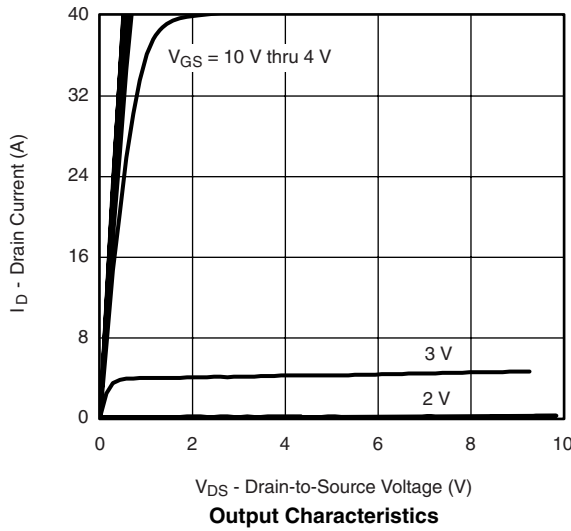
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



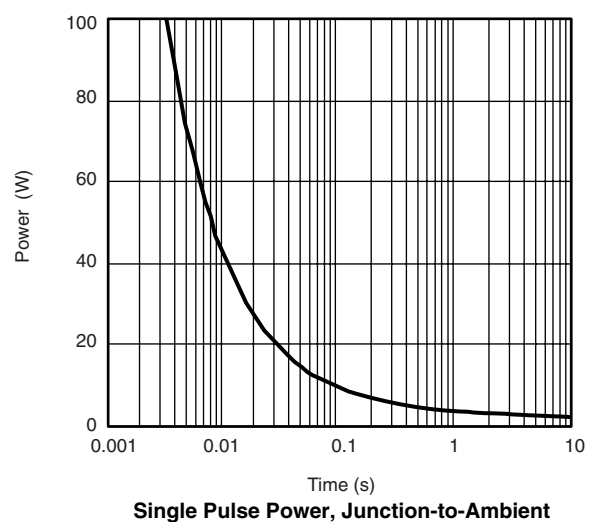
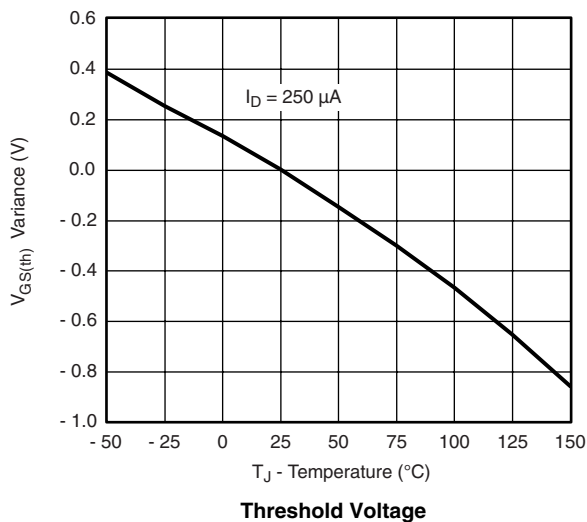
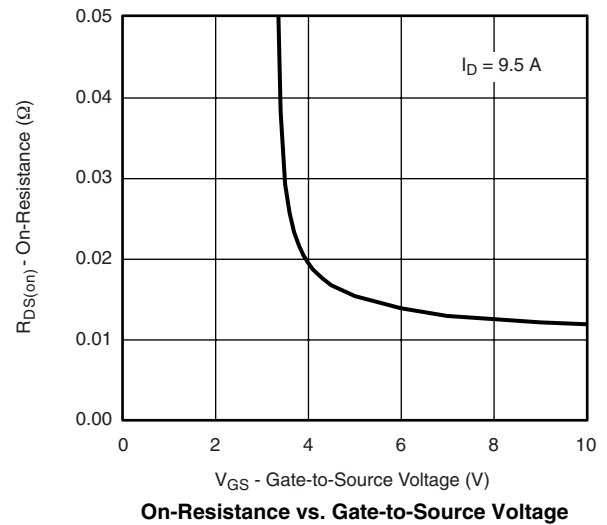
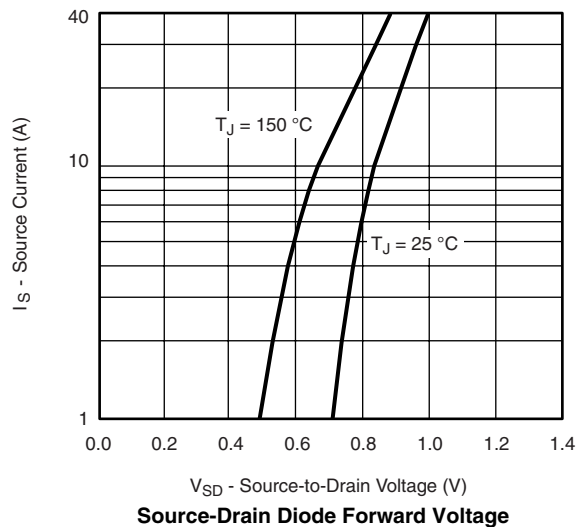
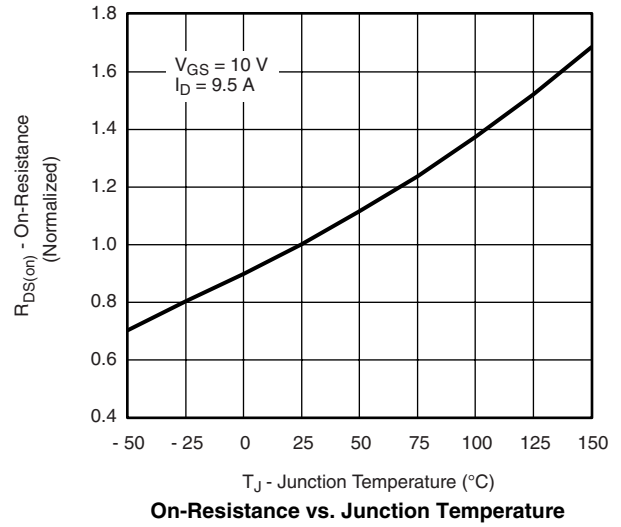
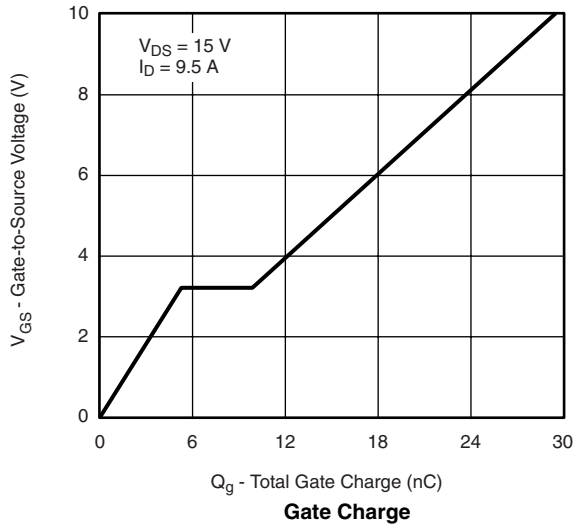
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



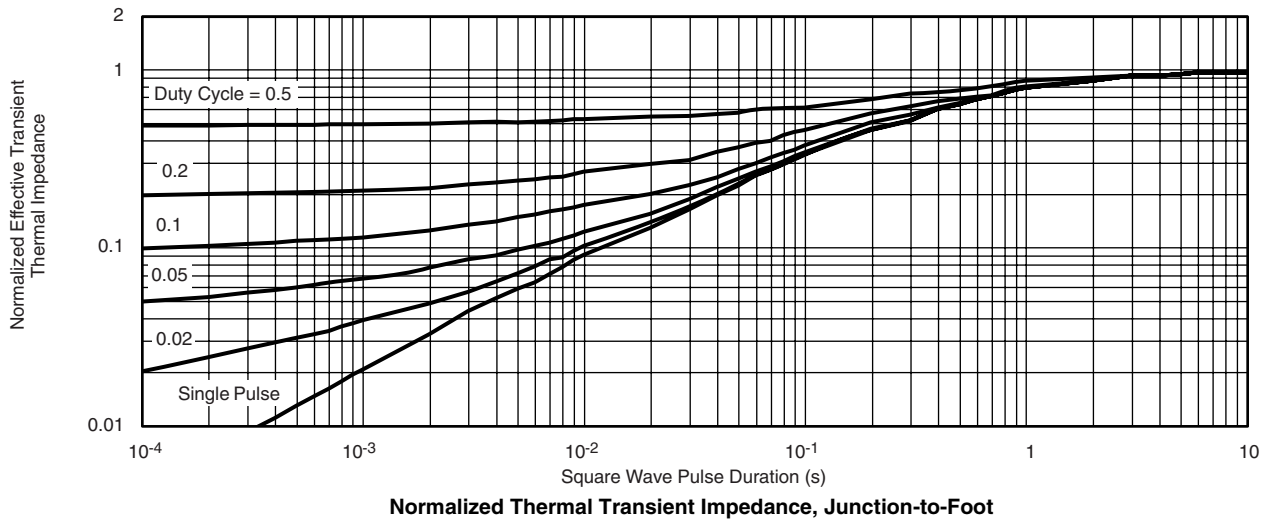
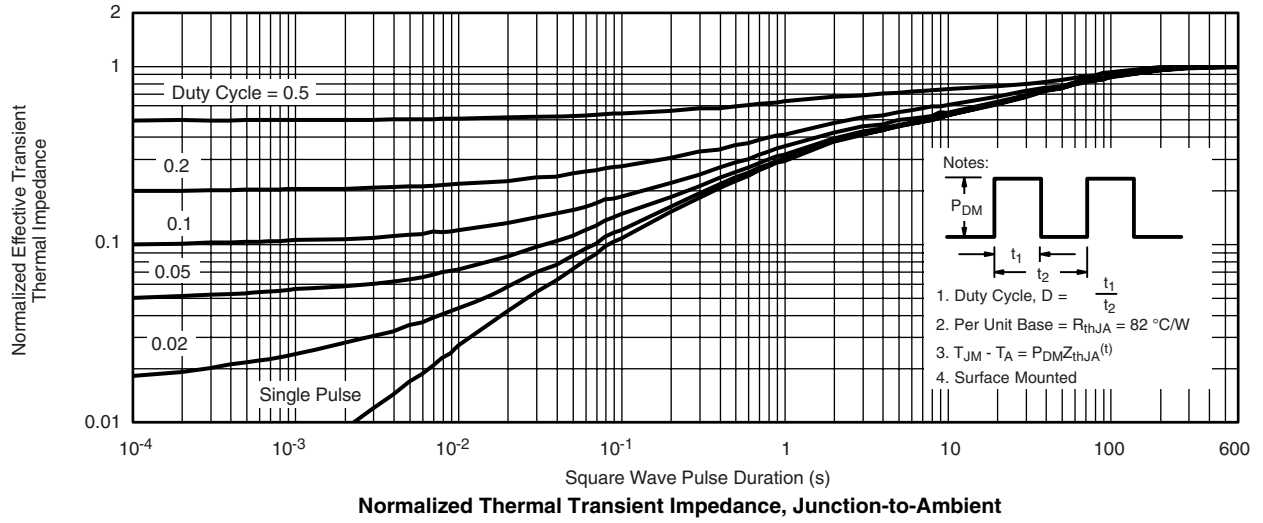
CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



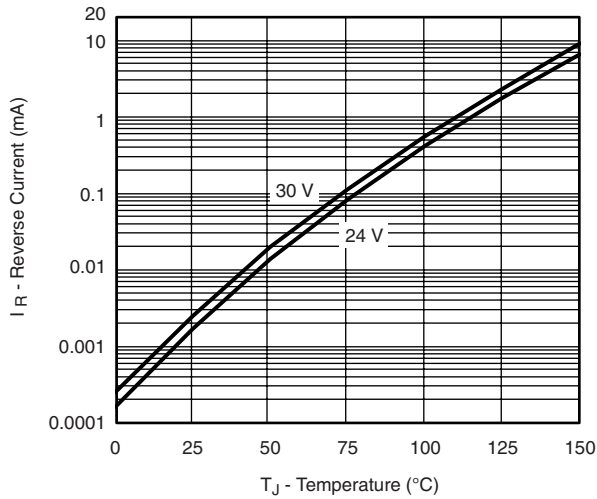
CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



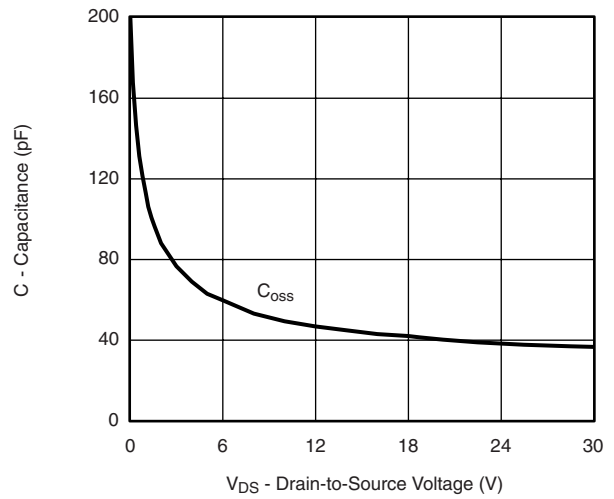
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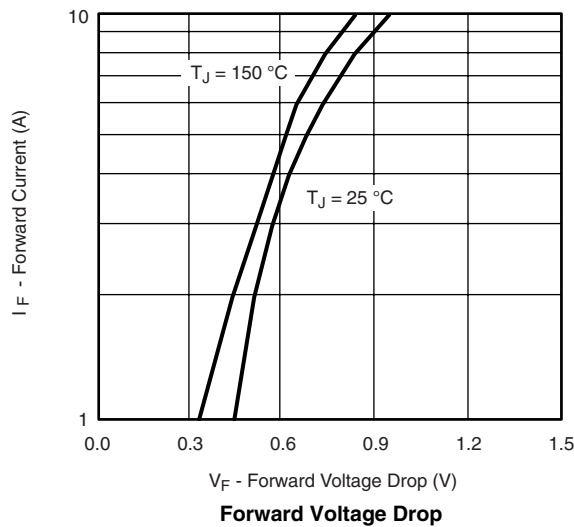
SCHOTTKY TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Reverse Current vs. Junction Temperature



Capacitance



Forward Voltage Drop

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